Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	283	(ultra-shallow or shallow) with (impurity adj region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 18:23
L2	44599	(drain or source or drain/source) with density	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 18:21
L3	24	1 and 2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 18:16
L4	22	3 and transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 18:16
L5	13	4 and CMOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 18:17
L6	2	("6333540" | "6433391").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/09/14 18:19
L8	305736	(drain or source or drain/source or channel or well) same density	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 18:23
L9	440	(ultra-shallow or shallow) same (impurity adj region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 18:23

L10	30	8 same 9	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 18:28
L11	18	@ad <= "20020107" and 10	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 18:28
L12	95	8 and 9	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 18:28
L13	87	12 and transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 18:28
L14	42	13 and CMOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 18:28
L15	22	@ad <= "20020107" and 14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 18:56
L16	17	15 not 11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 18:51
L17	41234	((low$3 or high$3) near3 density) same (source or drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 18:56

L18	3453	17 and "CMOS"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 18:56
L19	2863	18 and transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 18:55
L20	304	19 and (impurity adj region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 18:55
L21	331	((low$3 or high$3) near3 density) same (source or drain) same (impurity adj region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 18:56
L22	103	21 and "CMOS" and transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 18:56
L23	69	@ad <= "20020107" and 22	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 19:15
L24	67	23 not 16	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 18:57
L25	3	("4805147" | "5134581" | "5298764").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/09/14 19:08
L26	761	CMOS and LOCOS and ((shallow or (ultra adj shallow)) with (source or drain))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 19:42

L27	329	26 and (source and drain and gate and electrode and conductivity and transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 19:15
L28	232	@ad <= "20020107" and 27	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 19:41
L29	8	("4356623" | "5372957" | "5376566" | "5382533" | "5393683" | "5405791" | "5422506" | "5512771").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/09/14 19:38
L30	10017	(first conductivity) and (second conductivity) and source and drain and transistor and CMOS and impurity	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 19:39
L31	5559	30 and density	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 19:40
L32	4778	31 and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 19:40
L33	1337	32 and ((shallow or (ultra adj shallow)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 19:40
L34	803	@ad <= "20020107" and 33	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 19:48
L35	797	34 and gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 19:41

L36	311	35 and LOCOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 19:42
L37	223	36 not 28	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 19:46
L38	2521	438/197.ccls. or 438/199.ccls. or 438/218.ccls. or 438/225.ccls. or 438/299.ccls. or 438/301.ccls.	USPAT	OR	OFF	2005/09/14 20:08
L39	1008	38 and transistor and CMOS	USPAT	OR	OFF	2005/09/14 19:57
L40	775	@ad <= "20020107" and 39	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 19:57
L41	714	40 not 34	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 19:56
L42	700	41 not 28	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 19:55
L43	700	42 not 37	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 19:49
L44	714	40 not 34	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 20:05
L46	536	257/288.ccls. or "368".ccls. or "369".ccls.	USPAT	OR	OFF	2005/09/14 20:05
L47	147	46 and transistor and CMOS	USPAT	OR	OFF	2005/09/14 20:08

L48	98	@ad <= "20020107" and 47	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 20:05
L49	398	257/288.ccls. or "368".ccls. or "369".ccls.	US-PGPUB	OR	OFF	2005/09/14 20:05
L50	98	@ad <= "20020107" and 48	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 20:08
L51	61	50 and density	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/14 20:06
L52	1083	438/197.ccls. or 438/199.ccls. or 438/218.ccls. or 438/225.ccls. or 438/299.ccls. or 438/301.ccls.	US-PGPUB	OR	OFF	2005/09/14 20:08
L54	406	52 and transistor and CMOS	US-PGPUB	OR	OFF	2005/09/14 20:08
L55	98	@ad <= "20020107" and 54	US-PGPUB	OR	OFF	2005/09/14 20:08